**New Product** 



### SMMB912DK

**Vishay Siliconix** 

**RoHS** 

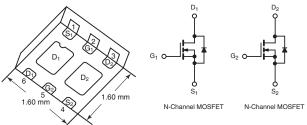
COMPLIANT

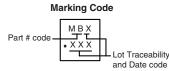
HALOGEN FREE

### Dual N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY								
V <sub>DS</sub> (V)	20							
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.216							
$R_{DS(on)}(\Omega)$ at $V_{GS} = 2.5 V$	0.268							
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = 1.8 V	0.375							
I <sub>D</sub> (A) <sup>a</sup>	1.5							
Configuration	Dual							

#### PowerPAK SC75-6L-Dual





#### **FEATURES**

- · High Quality Manufacturing Process Using SMM Process Flow
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
  - Small Footprint Area
- 100 % Rg Tested
- Compliant to RoHS Directive 2002/95/EC
- Find out more about Vishay's Medical Products at: www.vishay.com/medical-mosfets

#### **APPLICATION EXAMPLES**

- Medical Implantable Applications Including
- Drug Delivery Systems
- Defibrillators
- Pacemakers
- Hearing Aids
- Other Implantable Devices
- · Load Switch, PA Switch and Battery Switch for Portable Devices
- DC/DC Converter

#### **ORDERING INFORMATION** Package PowerPAK SC-75 SMMB912DK-T1-GE3

Lead (Pb)-free and Halogen-free

PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	20	V		
Gate-Source Voltage	V <sub>GS</sub>	± 8	v		
	T <sub>C</sub> = 25 °C <sup>a</sup>		1.5		
Continuous Drain Current /T 150 °C)	T <sub>C</sub> = 70 °C <sup>a</sup>	1	1.5	A	
Continuous Drain Current ( $T_J = 150 \ ^{\circ}C$ )	T <sub>A</sub> = 25 °C <sup>b, c</sup>	ID	1.5		
	T <sub>A</sub> = 70 °C <sup>b, c</sup>		1.4		
Pulsed Drain Current	I <sub>DM</sub>	5			
Continuous Source Drain Diada Current	T <sub>C</sub> = 25 °C <sup>a</sup>	I	1.5		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C <sup>b, c</sup>	I <sub>S</sub>	0.9		
	T <sub>C</sub> = 25 °C		3.1	w	
Maximum Dawar Dissinction	T <sub>C</sub> = 70 °C	P	2.0		
Maximum Power Dissipation	T <sub>A</sub> = 25 °C <sup>b, c</sup>	P <sub>D</sub>	1.1	vv	
	T <sub>A</sub> = 70 °C <sup>b, c</sup>		0.7	1	
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C		
Soldering Recommendations (Peak Temperature		260			

### Vishay Siliconix



THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	90	115	80 M				
Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	32	40	°C/W				

Notes

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 125 °C/W.

SPECIFICATIONS $T_J = 25 \ ^{\circ}C$ ,	unless otherv	wise noted					
PARAMETER	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static				-	-		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	20	-	-	V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$		L 050 ··· A			-	m\//ºC
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1	I <sub>D</sub> = 250 μA	-	- 2	-	mV/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.4	-	1	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	= 0 V, V <sub>GS</sub> = ± 8 V	-	-	± 100	nA
Zaro Cata Valtaga Drain Currant		$V_{GS} = 0 V$	V <sub>DS</sub> = 20 V	-	-	1	μA
Zero Gate Voltage Drain Current	IDSS	$V_{GS} = 0 V$	$V_{DS}$ = 20 V, $T_J$ = 55 °C	-	-	10	μΑ
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 4.5 V$	$V_{DS} \ge 5 V$	5	-	-	Α
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 1.8 A	-	0.180	0.216	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 2.5 V$	I <sub>D</sub> = 1.6 A	-	0.223	0.268	Ω
		V <sub>GS</sub> = 1.8 V	I <sub>D</sub> = 0.3 A	-	0.300	0.375	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> :	-	3	-	S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	95	-	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 10 V, f = 1 MHz	-	24	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	11	-	
Total Cata Charge	0	V <sub>GS</sub> = 8 V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.8 A	-	2	3	
Total Gate Charge	Qg			-	1.2	1.8	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>GS</sub> = 4.5 V	$V_{DS} = 10 \text{ V}, I_D = 1.8 \text{ A}$	-	0.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	1		-	0.15	-	
Gate Resistance	Rg		f = 1 MHz	0.5	2.5	5	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			-	5	10	
Rise Time	t <sub>r</sub>	V <sub>DD</sub> =	= 10 V, R <sub>L</sub> = 7.1 Ω	-	10	20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 1.4 \text{ A},$	$V_{GEN}$ = 4.5 V, $R_g$ = 1 $\Omega$	-	24	36	
Fall Time	t <sub>f</sub>			-	8	16	
Turn-On Delay Time	t <sub>d(on)</sub>			-	2	4	ns
Rise Time	t <sub>r</sub>	V <sub>DD</sub> =	-	9	18		
Turn-Off Delay Time	t <sub>d(off)</sub>	I <sub>D</sub> ≅ 1.4 A	-	8	16	1	
Fall Time	t <sub>f</sub>	]		-	7	14	
Source-Drain Body Diode Characteristic	s	·			•		
Continuous Source-Drain Diode Current <sup>c</sup>	I <sub>S</sub>	T <sub>C</sub> = 25 °C		-	-	1.5	
Pulse Diode Forward Current	I <sub>SM</sub>		-	-	5	A	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =	1.4 A, V <sub>GS</sub> = 0 V	-	0.7	1.2	V



**Vishay Siliconix** 

<b>SPECIFICATIONS</b> $T_J = 25 \text{ °C}$ , unless otherwise noted										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT				
Source-Drain Body Diode Characteristics										
Body Diode Reverse Recovery Time	t <sub>rr</sub>		-	9	18	ns				
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 1.4 A, dl/dt = 100 A/μs, T <sub>.I</sub> = 25 °C	-	3	6	nC				
Reverse Recovery Fall Time	t <sub>a</sub>	$F = 1.4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_{\text{J}} = 25 \text{ C}$	-	6	-	20				
Reverse Recovery Rise Time	t <sub>b</sub>		-	3	-	ns				

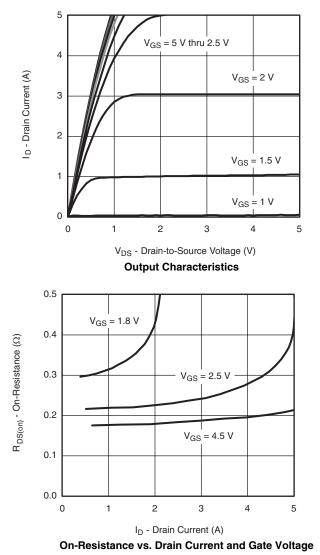
Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

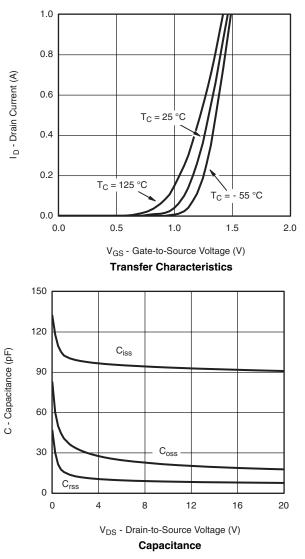
b. Guaranteed by design, not subject to production testing.

c. Package limited.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

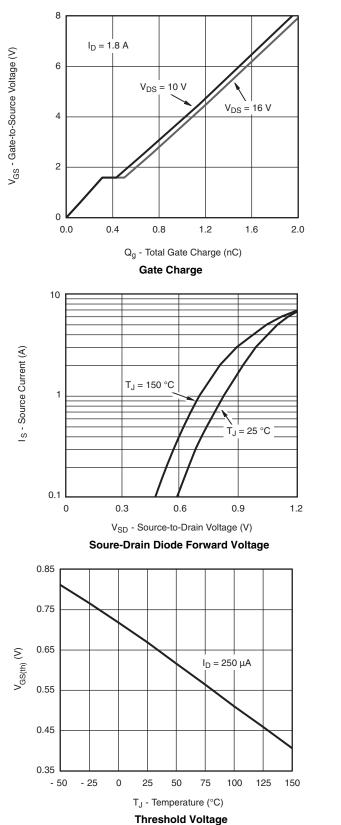


**TYPICAL CHARACTERISTICS**  $T_A = 25$  °C, unless otherwise noted

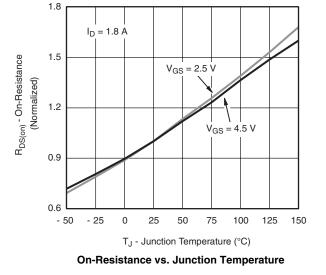


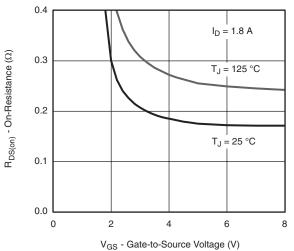
Vishay Siliconix



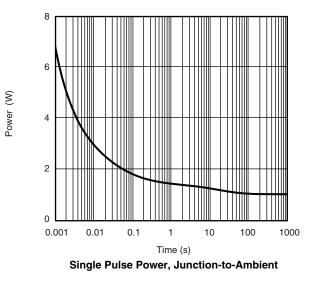


### **TYPICAL CHARACTERISTICS** $T_A = 25 \degree C$ , unless otherwise noted







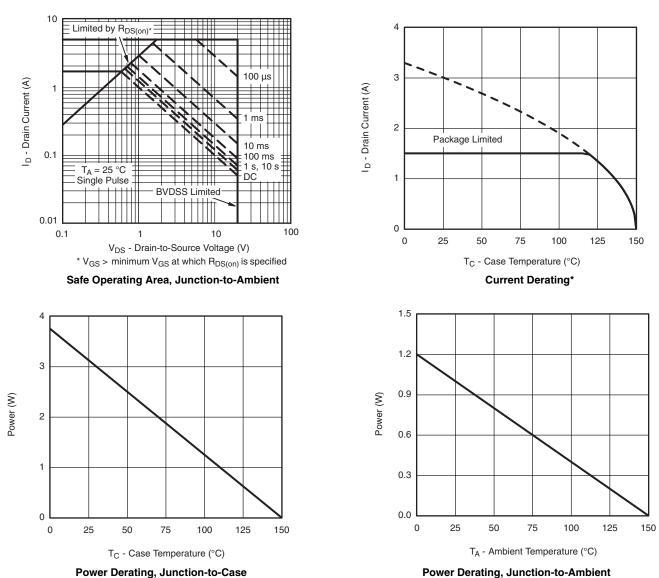




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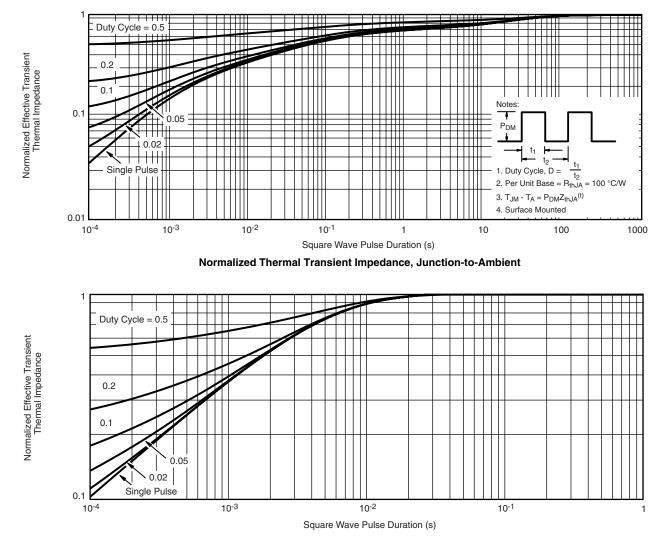
### **TYPICAL CHARACTERISTICS** $T_A = 25$ °C, unless otherwise noted

\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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### **TYPICAL CHARACTERISTICS** $T_A = 25 \text{ °C}$ , unless otherwise noted



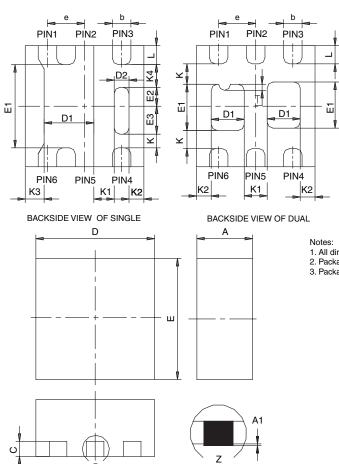
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?65459">www.vishay.com/ppg?65459</a>.

# Package Information

### Vishay Siliconix





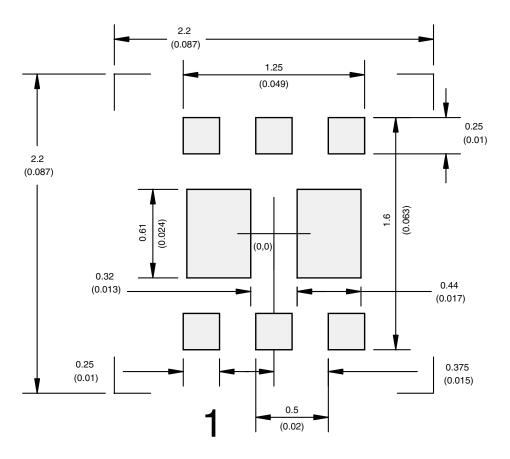
- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

DETAIL Z

		SINGLE PAD					DUAL PAD					
DIM	М	ILLIMETER	RS		INCHES		Μ	ILLIMETEF	rs		INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
е		0.50 BSC		0.020 BSC				0.50 BSC			0.020 BSC	
К		0.180 TYP			0.007 TYP			0.245 TYP			0.010 TYP	
K1		0.275 TYP			0.011 TYP		0.320 TYP			0.013 TYP		
K2		0.200 TYP			0.008 TYP		0.200 BSC			0.008 TYP		
K3		0.255 TYP			0.010 TYP							
K4		0.300 TYP		0.012 TYP								
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
Т							0.03	0.08	0.13	0.001	0.003	0.005
ECN: C-07431 – Rev. C, 06-Aug-07 DWG: 5935												



### **RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Dual**



Dimensions in mm/(Inches)

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